

MOSFET – Power, Dual, N-Channel, POWERTRENCH[®], Power Clip, Asymmetric

25 V

NTMFD1D4N02P1E

Features

- Small Footprint (5x6mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- These are Pb-free, Halogen Free / BFR Free and are RoHS Compliant

Typical Applications

- DC-DC Converters
- System Voltage Rails

MAXIMUM RATINGS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise stated)

Parameter			Sym bol	Q1	Q2	Unit
Drain-to-Source Voltage			V_{DSS}	25	25	V
Gate-to-Source Voltage			V_{GS}	+16V -12V	+16V -12V	V
Continuous Drain Current $R_{\theta JC}$ (Note 3)	Steady State	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	74	155	A
		$T_C = 85\text{ }^{\circ}\text{C}$		53	112	
Power Dissipation $R_{\theta JC}$ (Note 3)		$T_A = 25\text{ }^{\circ}\text{C}$	P_D	25	41	W
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 3)	Steady State	$T_A = 25\text{ }^{\circ}\text{C}$	I_D	20	36	A
		$T_A = 85\text{ }^{\circ}\text{C}$		14	26	
Power Dissipation $R_{\theta JA}$ (Notes 1, 3)		$T_A = 25\text{ }^{\circ}\text{C}$	P_D	2.1	2.3	W
Continuous Drain Current $R_{\theta JA}$ (Notes 2, 3)	Steady State	$T_A = 25\text{ }^{\circ}\text{C}$	I_D	13	24	A
		$T_A = 85\text{ }^{\circ}\text{C}$		10	17	
Power Dissipation $R_{\theta JA}$ (Notes 2, 3)		$T_A = 25\text{ }^{\circ}\text{C}$	P_D	0.96	1.0	W
Pulsed Drain Current	$T_A = 25\text{ }^{\circ}\text{C}, t_p = 10\text{ }\mu\text{s}$		I_{DM}	325	552	A
Single Pulse Drain-to-Source Avalanche Energy Q1: $I_L = 9.4\text{ A}_{pk}, L = 3\text{ mH}$ (Note 4) Q2: $I_L = 20.1\text{ A}_{pk}, L = 3\text{ mH}$ (Note 4)			E_{AS}	134	604	mJ
Operating Junction and Storage Temperature Range			T_J, T_{stg}	-55 to 150		$^{\circ}\text{C}$
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)			T_L	260		$^{\circ}\text{C}$

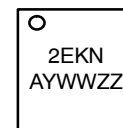
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

FET	$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
Q1	25 V	3.3 m Ω @ 10 V	74 A
		4.2 m Ω @ 4.5 V	
Q2	25 V	1.1 m Ω @ 10 V	155 A
		1.33 m Ω @ 4.5 V	



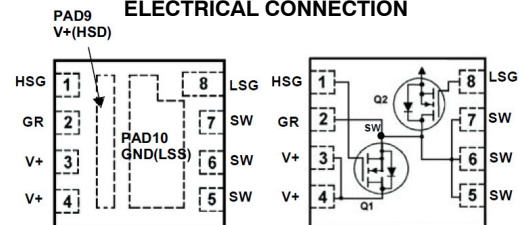
PQFN8
POWER CLIP
CASE 483AR

MARKING DIAGRAM



2EKN = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

ELECTRICAL CONNECTION



ORDERING INFORMATION

Device	Package	Shipping [†]
NTMFD1D4N02P1E	PQFN8 (Pb-Free)	3000 / Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](http://www.onsemi.com/BRD8011/D).

NTMFD1D4N02P1E

Table 1. THERMAL RESISTANCE RATINGS

Parameter	Symbol	Q1 Max	Q2 Max	Units
Junction-to-Case – Steady State (Note 1, 3)	$R_{\theta JC}$	4.4	2.9	°C/W
Junction-to-Ambient – Steady State (Note 1, 3)	$R_{\theta JA}$	60	55	
Junction-to-Ambient – Steady State (Note 2, 3)	$R_{\theta JA}$	130	120	

1. Surface-mounted on FR4 board using 1 in² pad size, 2 oz Cu pad.
2. Surface-mounted on FR4 board using minimum pad size, 2 oz Cu pad.
3. The entire application environment impacts the thermal resistance values shown. They are not constants and are only valid for the particular conditions noted. Actual continuous current will be limited by thermal & electro-mechanical application board design. $R_{\theta CA}$ is determined by the user's board design.
4. Q1 100% UIS tested at $L = 0.1$ mH, $I_{AS} = 16.5$ A.
Q2 100% UIS tested at $L = 0.1$ mH, $I_{AS} = 36$ A.

Table 2. ELECTRICAL CHARACTERISTICS ($T_J = 25$ °C unless otherwise stated)

Parameter	Symbol	Test Condition	FET	Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = 250$ μ A	Q1	25			V
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = 1$ mA	Q2	25			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS} / T_J$	$I_D = 250$ μ A, ref to 25 °C	Q1		16		mV/°C
		$I_D = 1$ mA, ref to 25 °C	Q2		19		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0$ V, $V_{DS} = 20$ V	$T_J = 25$ °C	Q1		10	μ A
				Q2		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = +16$ V / -12 V	Q1			± 100	nA
		$V_{DS} = 0$ V, $V_{GS} = +16$ V / -12 V	Q2			± 100	

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250$ μ A	Q1	1.2	1.54	2.0	V
		$V_{GS} = V_{DS}$, $I_D = 800$ μ A	Q2	1.2	1.55	2.0	
Threshold Temperature Coefficient	$V_{GS(TH)} / T_J$	$I_D = 250$ μ A, ref to 25 °C	Q1		-4.3		mV/°C
		$I_D = 800$ μ A, ref to 25 °C	Q2		-4.4		
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 20$ A	Q1		2.6	3.3	m Ω
		$V_{GS} = 4.5$ V, $I_D = 18$ A			3.4	4.2	
		$V_{GS} = 10$ V, $I_D = 37$ A	Q2		0.81	1.1	
		$V_{GS} = 4.5$ V, $I_D = 33$ A			1.04	1.33	
Forward Transconductance	g_{FS}	$V_{DS} = 5$ V, $I_D = 20$ A	Q1		125		
		$V_{DS} = 5$ V, $I_D = 37$ A	Q2		285		
Gate Resistance	R_G	$T_A = 25$ °C	Q1		0.44		Ω
			Q2		0.6		

CHARGES & CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, V _{DS} = 13 V, f = 1 MHz	Q1		1180		pF
			Q2		3603		
Output Capacitance	C _{OSS}		Q1		320		pF
			Q2		940		
Reverse Capacitance	C _{RSS}		Q1		22		pF
			Q2		64		

5. Pulse Test: pulse width ≤ 300 μ s, duty cycle $\leq 2\%$
6. Switching characteristics are independent of operating junction temperatures

NTMFD1D4N02P1E

Table 2. ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise stated) (continued)

Parameter	Symbol	Test Condition	FET	Min	Typ	Max	Unit
CHARGES & CAPACITANCES							
Total Gate Charge	$Q_{G(TOT)}$	Q1: $V_{GS} = 4.5\text{V}$, $V_{DS} = 13\text{V}$, $I_D = 20\text{A}$ Q2: $V_{GS} = 4.5\text{V}$, $V_{DS} = 13\text{V}$, $I_D = 37\text{A}$	Q1		7.2		nC
			Q2		21.5		
Gate-to-Drain Charge	Q_{GD}		Q1		1.35		nC
			Q2		3.9		
Gate-to-Source Charge	Q_{GS}		Q1		3.15		nC
			Q2		9.1		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 13\text{V}$, $I_D = 20\text{A}$	Q1		16.4		nC
		$V_{GS} = 10\text{V}$, $V_{DS} = 13\text{V}$, $I_D = 37\text{A}$	Q2		48.6		

SWITCHING CHARACTERISTICS, $V_{GS} = 4.5\text{V}$ (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{V}$ Q1: $I_D = 20\text{A}$, $V_{DD} = 13\text{V}$, $R_G = 6\Omega$ Q2: $I_D = 37\text{A}$, $V_{DD} = 13\text{V}$, $R_G = 6\Omega$	Q1		11.6		ns
			Q2		21.4		
Rise Time	$t_{r(ON)}$		Q1		2.7		ns
			Q2		8.7		
Turn-Off Delay Time	$t_{d(OFF)}$		Q1		15.6		ns
			Q2		30.7		
Fall Time	t_f		Q1		3.2		ns
			Q2		8.5		

SWITCHING CHARACTERISTICS, $V_{GS} = 10\text{V}$ (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{V}$ Q1: $I_D = 20\text{A}$, $V_{DD} = 13\text{V}$, $R_G = 6\Omega$ Q2: $I_D = 37\text{A}$, $V_{DD} = 13\text{V}$, $R_G = 6\Omega$	Q1		7.9		ns
			Q2		10.2		
Rise Time	$t_{r(ON)}$		Q1		1.1		ns
			Q2		3.3		
Turn-Off Delay Time	$t_{d(OFF)}$		Q1		21.3		ns
			Q2		48.9		
Fall Time	t_f		Q1		2.2		ns
			Q2		7.4		

SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{V}$, $I_S = 20\text{A}$	$T_J = 25\text{ }^{\circ}\text{C}$	Q1		0.8	1.2	V
			$T_J = 125\text{ }^{\circ}\text{C}$			0.7		
		$V_{GS} = 0\text{V}$, $I_S = 37\text{A}$	$T_J = 25\text{ }^{\circ}\text{C}$	Q2		0.8	1.2	
			$T_J = 125\text{ }^{\circ}\text{C}$			0.65		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{V}$, Q1: $I_S = 20\text{A}$, $dI/dt = 100\text{A}/\mu\text{s}$ Q2: $I_S = 37\text{A}$, $dI/dt = 300\text{A}/\mu\text{s}$		Q1		21.4		ns
				Q2		36.5		
Reverse Recovery Charge	Q_{RR}			Q1		8.3		nC
				Q2		21.9		

5. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

6. Switching characteristics are independent of operating junction temperatures

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS FOR Q1

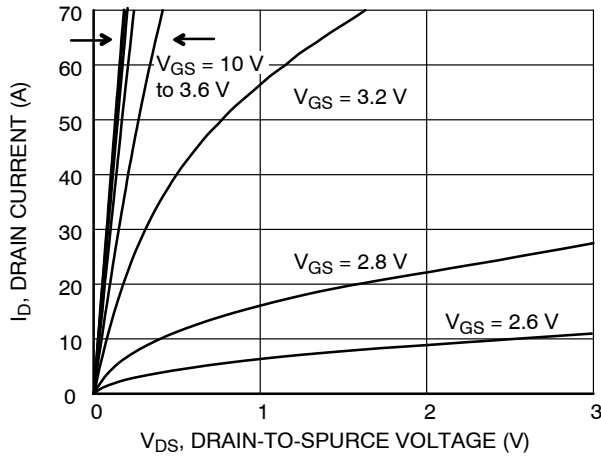


Figure 1. On-Region Characteristics

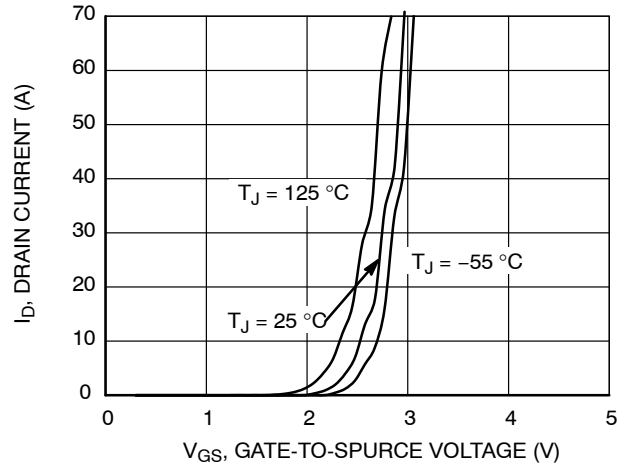


Figure 2. Transfer Characteristics

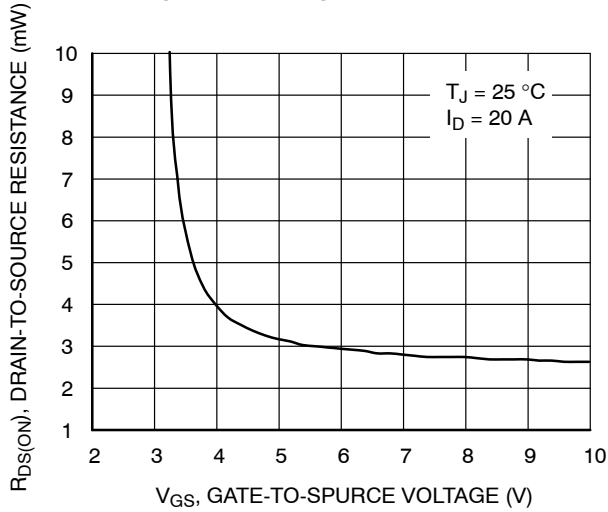


Figure 3. On-Resistance vs. Gate-to-Source Voltage

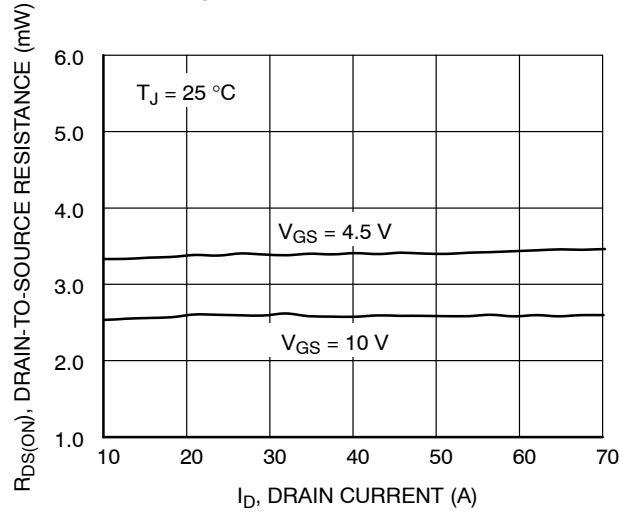


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

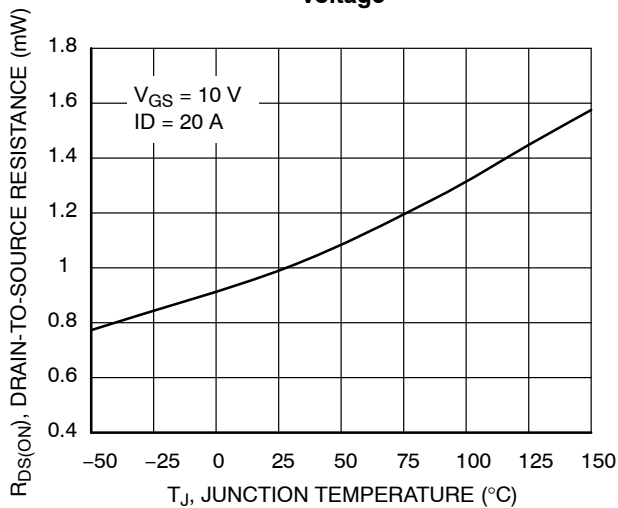


Figure 5. On-Resistance Variation with Temperature

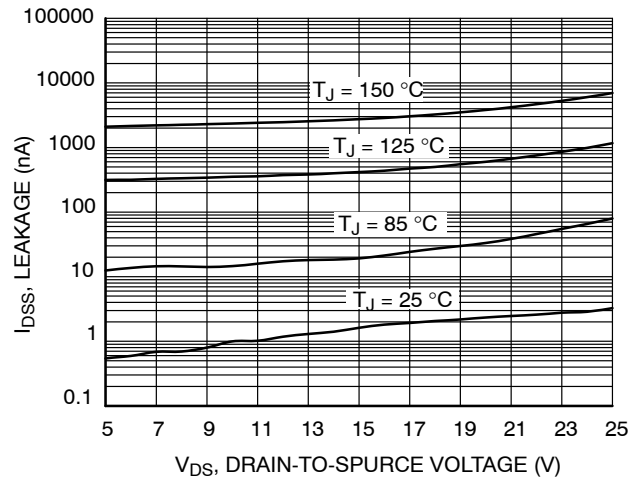


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTMFD1D4N02P1E

TYPICAL CHARACTERISTICS FOR Q1 (continued)

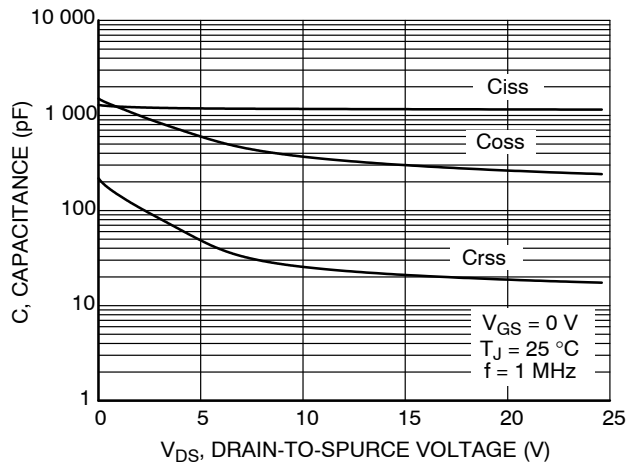


Figure 7. Capacitance Variation

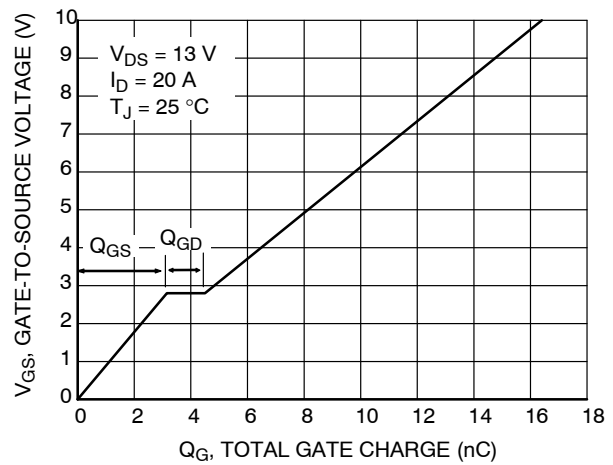


Figure 8. Gate-to-Source vs. Total Charge

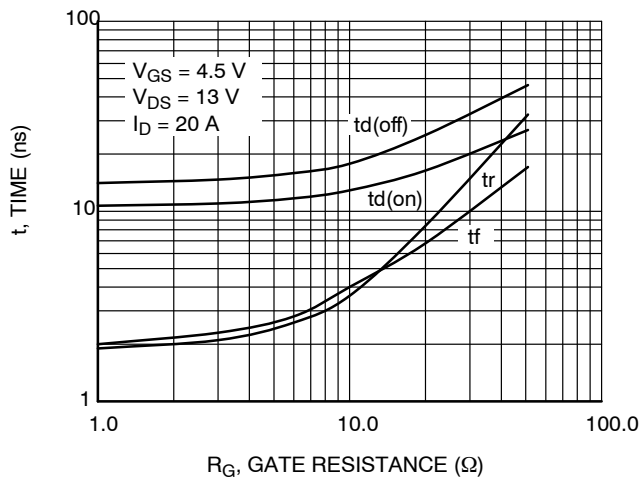


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

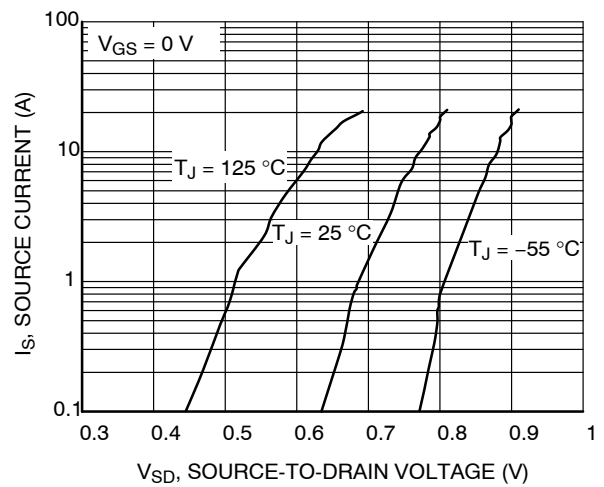


Figure 10. Diode Forward Voltage vs. Current

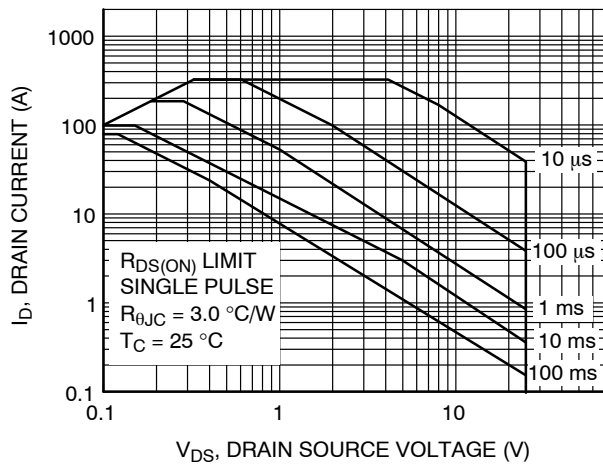


Figure 11. Maximum Rated Forward Biased Safe Operating Area

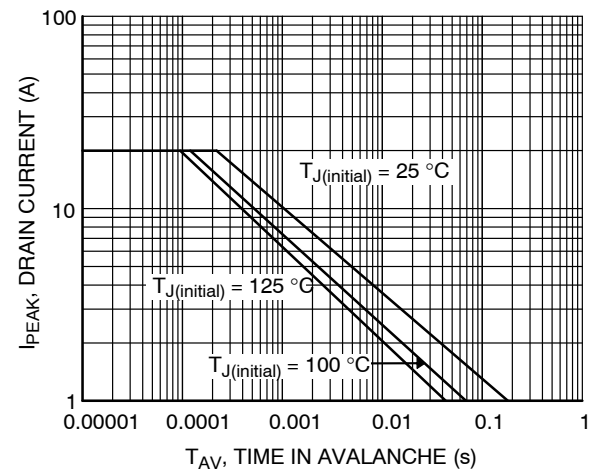


Figure 12. Maximum Drain Current vs. Time in Avalanche

NTMFD1D4N02P1E

TYPICAL CHARACTERISTICS FOR Q1 (continued)

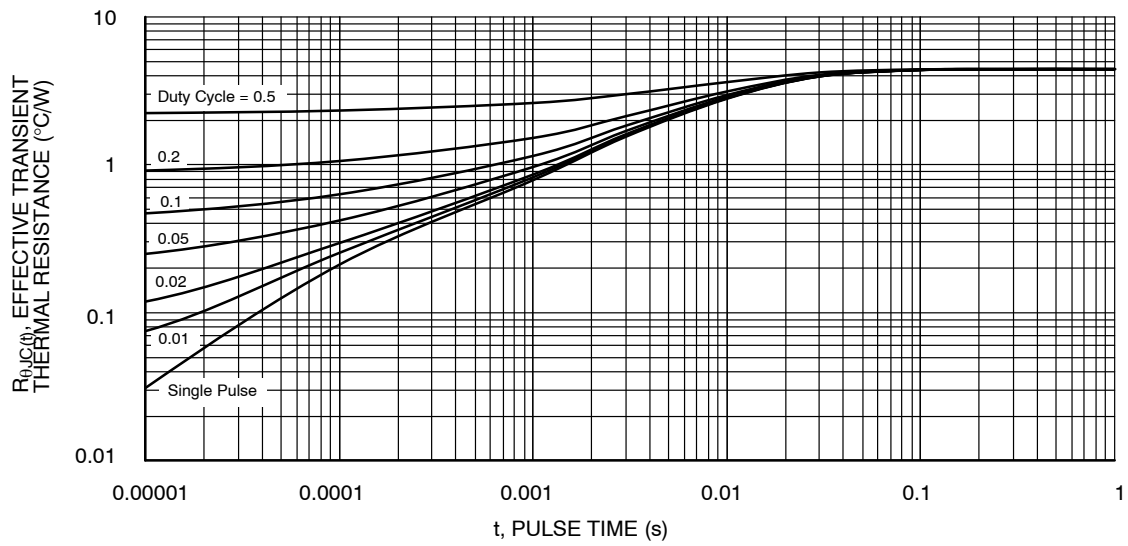


Figure 13. Thermal Response

NTMFD1D4N02P1E

TYPICAL CHARACTERISTICS FOR Q2

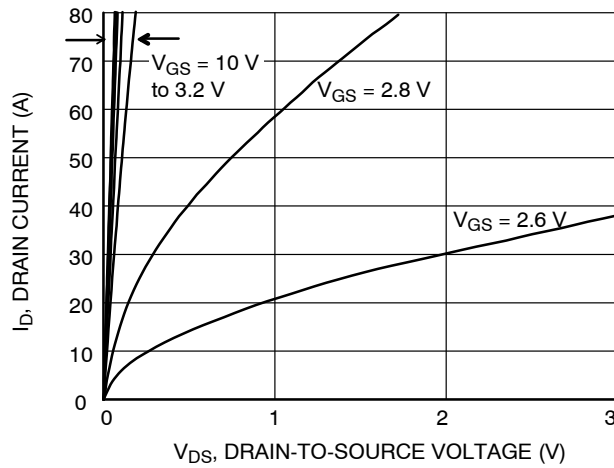


Figure 14. On-Region Characteristics

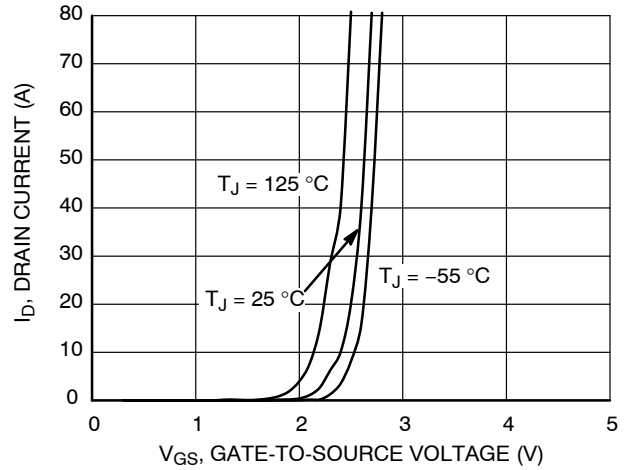


Figure 15. Transfer Characteristics

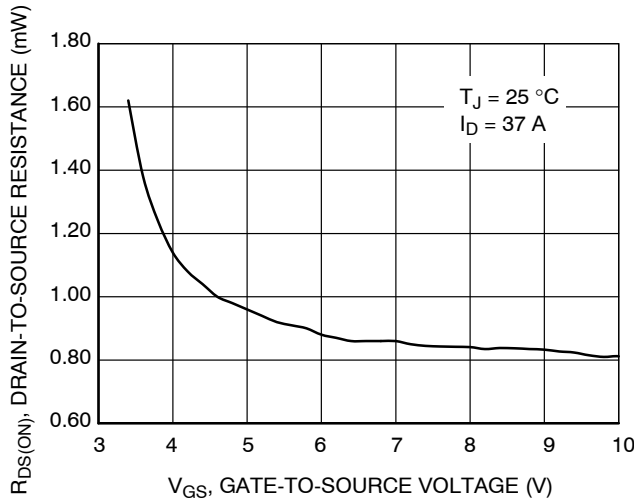


Figure 16. On-Resistance vs. Gate-to-Source Voltage

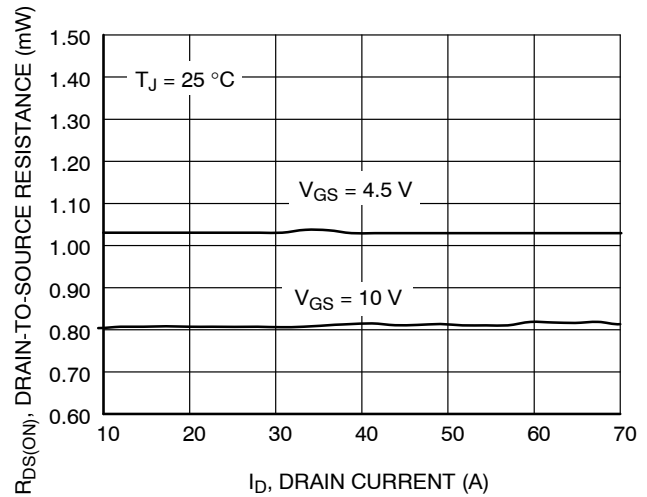


Figure 17. On-Resistance vs. Drain Current and Gate Voltage

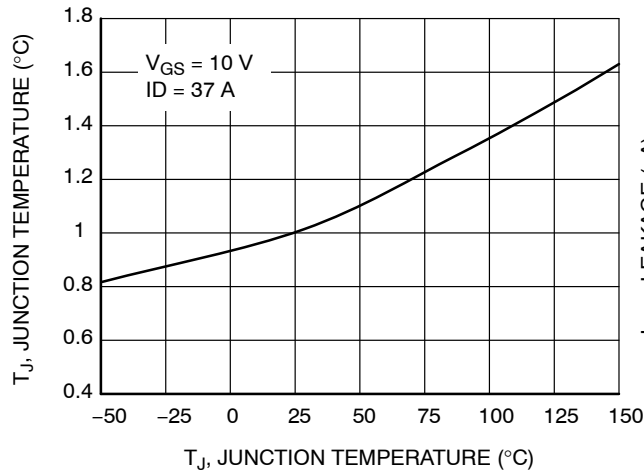


Figure 18. On-Resistance Variation with Temperature

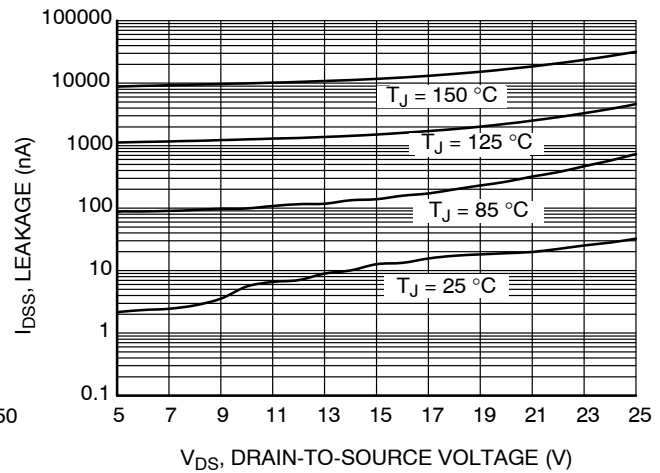


Figure 19. Drain-to-Source Leakage Current vs. Voltage

NTMFD1D4N02P1E

TYPICAL CHARACTERISTICS FOR Q2 (continued)

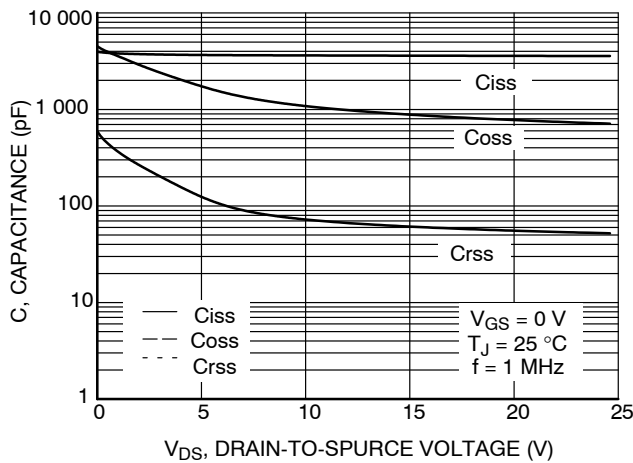


Figure 20. Capacitance Variation

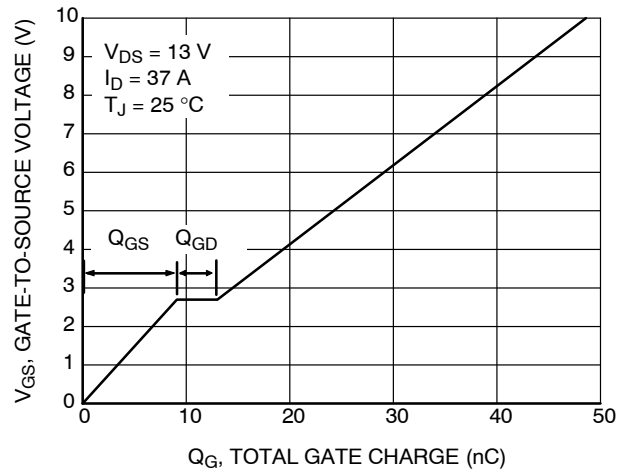


Figure 21. Gate-to-Source vs. Total Charge

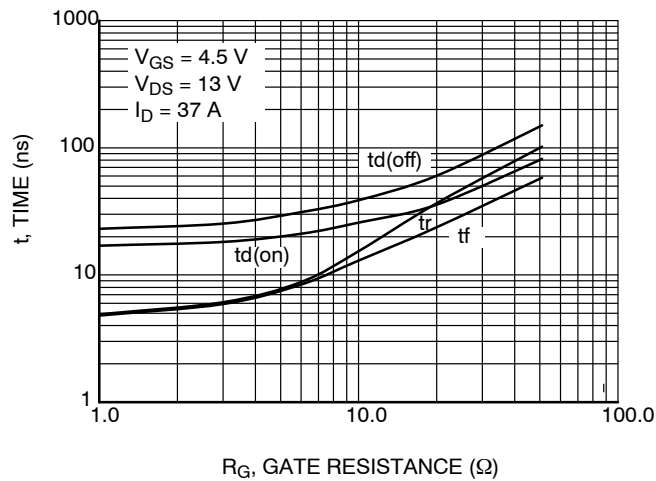


Figure 22. Resistive Switching Time Variation vs. Gate Resistance

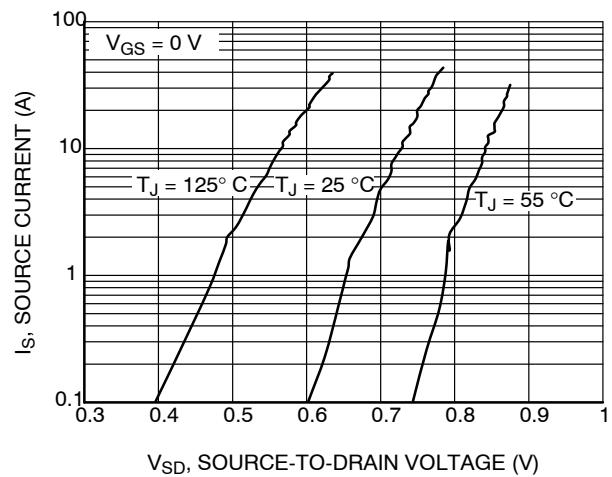


Figure 23. Diode Forward Voltage vs. Current

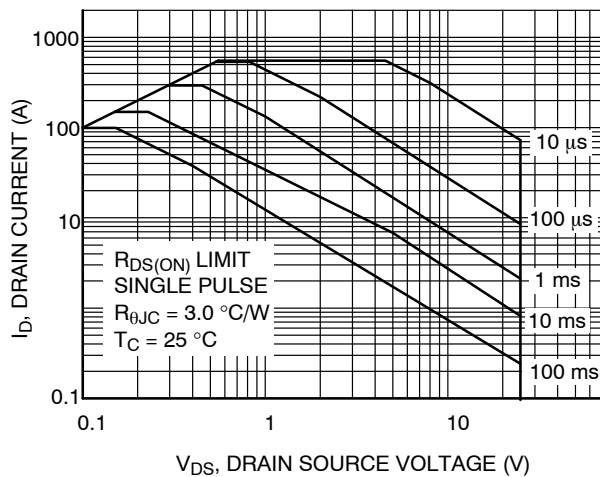


Figure 24. Maximum Rated Forward Biased Safe Operating Area

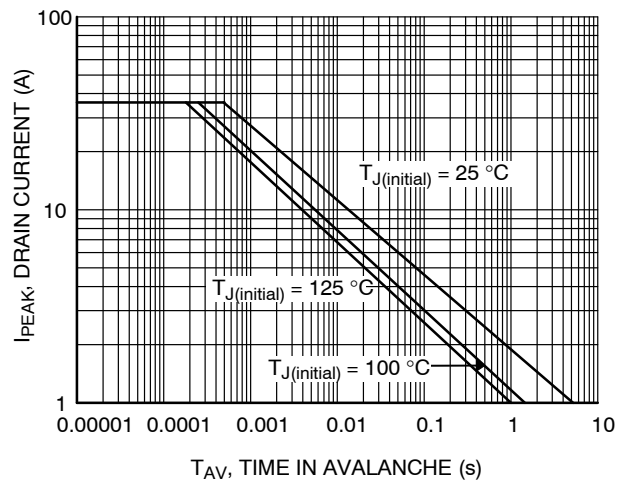


Figure 25. Maximum Drain Current vs. Time in Avalanche

NTMFD1D4N02P1E

TYPICAL CHARACTERISTICS FOR Q2 (continued)

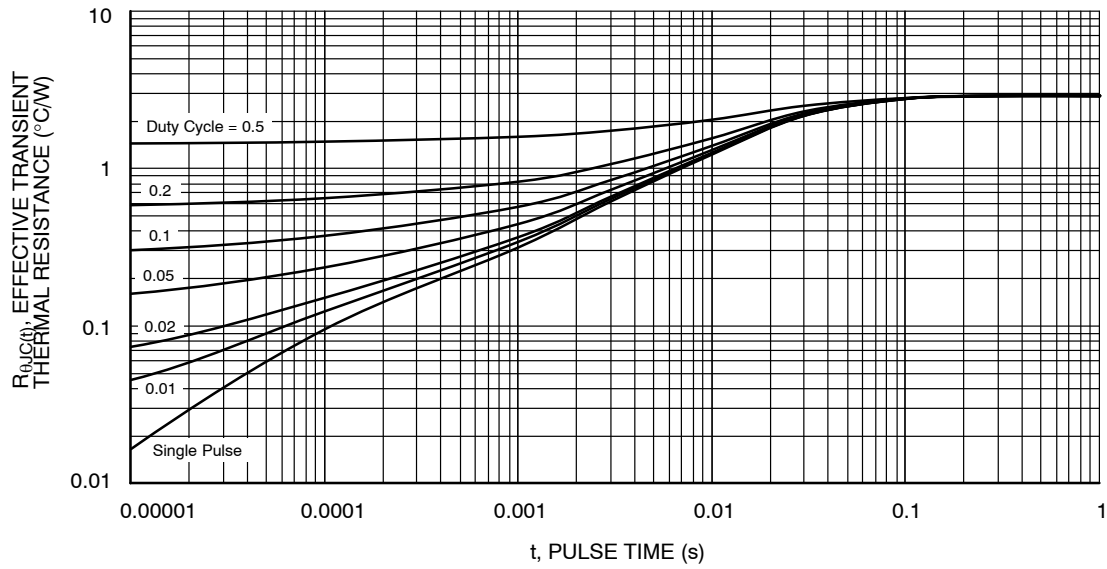


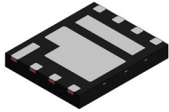
Figure 26. Thermal Response

NTMFD1D4N02P1E

REVISION HISTORY

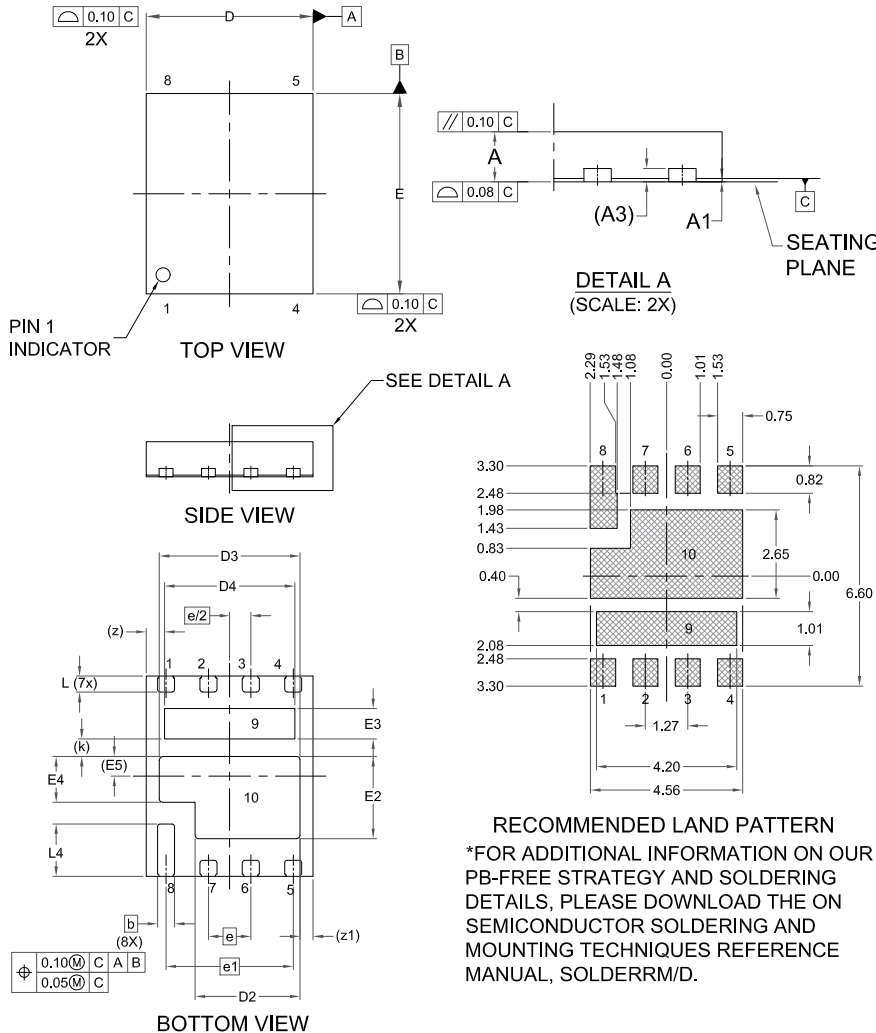
Revision	Description of Changes	Date
2	Document rebranded to onsemi format.	11/5/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.



PQFN8 5.00x6.00x0.75, 1.27P
CASE 483AR
ISSUE D

DATE 06 NOV 2023



NOTES: UNLESS OTHERWISE SPECIFIED

- A) DOES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229, DATED 11/2001.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	-	0.05
A3	0.20 REF		
b	0.51 BSC		
D	4.90	5.00	5.10
D2	3.05	3.15	3.25
D3	4.12	4.22	4.32
D4	3.80	3.90	4.00
E	5.90	6.00	6.10
E2	2.36	2.46	2.56
E3	0.81	0.91	1.01
E4	1.27	1.37	1.47
E5	0.59 REF		
e	1.27 BSC		
e/2	0.635 BSC		
e1	3.81 BSC		
k	0.52 REF		
L	0.38	0.48	0.58
L4	1.47	1.57	1.67
z	0.55 REF		
z1	0.39 REF		

DOCUMENT NUMBER: 98AON13666G

Electronic versions are uncontrolled except when accessed directly from the Document Repository.
Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.

DESCRIPTION: PQFN8 5.00x6.00x0.75, 1.27P

PAGE 1 OF 1

onsemi and Onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales